

MBD2057-H20X Planar Tunnel Diode



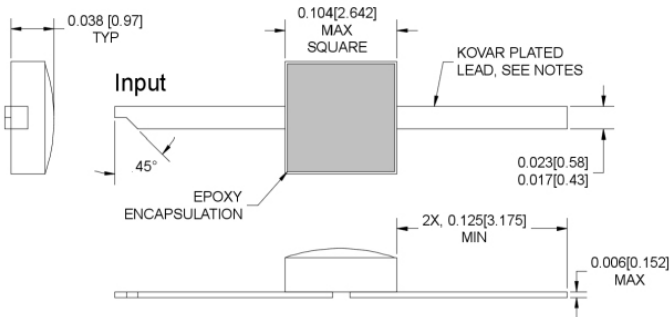
Technical Characteristics

| Product Features                     |
|--------------------------------------|
| Rugged Germanium Planar Construction |
| Excellent Temperature Stability      |
| No DC Bias Required                  |
| Wide Video Bandwidth                 |

| Product Description                                                                                                                                                                                                                                        |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| EclipseMDI MBD2057-H20X, is a zero-bias, rugged Planar Tunnel Diode constructed with Germanium Planar. This tunnel diode exhibits excellent temperature stability, wide video bandwidth. The MBD2057 is also available in hermetic (H20) ceramic packages. |

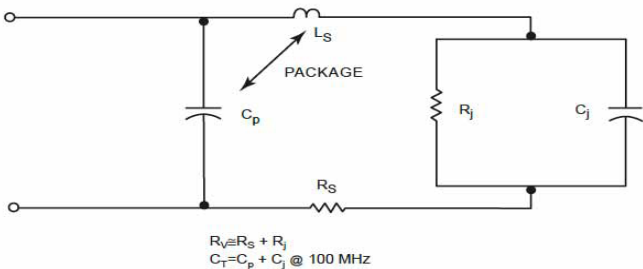
| Maximum Ratings                                      |
|------------------------------------------------------|
| Storage Temperature.....-65° to +125°C               |
| Operating Temperature.....-65° to +110°C             |
| Input Power Handling.....+17dBm CW<br>or 3 ERG spike |
| Soldering Temperature.....+160° C                    |

H20X Non-Hermetic

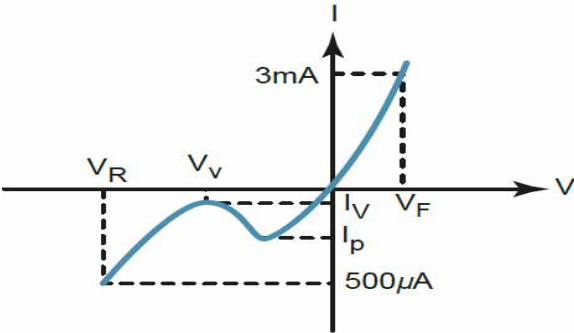


| Parameters | Specifications                        |     |         |     |        |
|------------|---------------------------------------|-----|---------|-----|--------|
|            | Conditions                            | MIN | Typical | MAX | UNITS  |
| Ip         |                                       | 200 |         | 300 | µA     |
| Cj         | Vr=Vv,<br>f=100MHz                    |     |         | .30 | pF     |
| K[Y]       | Pin=-20dBm<br>RjLoad)=10K,<br>f=10GHz |     | 750     |     | mV/mW  |
| Rv         |                                       |     | 130     |     | Ω Ohms |
| Ip/Iv      |                                       | 2.5 |         |     |        |
| Vr         | If=500µA                              |     | 410     |     | mV     |
| Vf         | If=3mA                                |     |         | 130 | mV     |

Diode equivalent circuit



Back diode parameters



About EclipseMDI

ECLIPSE Microdevices is located in San Jose, California. ECLIPSE has been developing high performance analog semiconductors for use in wireless radio frequency (RF), microwave, and millimeter wave for commercial and industrial applications. ECLIPSE has formed a strategic alliances - with foundries that features leading state-of-the-art process technologies and with manufacturing facilities for high-volume production of innovative RFIC's.

Product Export Classification

ECCN: EAR 99 (unless otherwise specified)  
HTS: 8542330000